



TLV809 3 引脚电源电压监控器

1 特性

- 高精度电源电压监控器: 2.5V、3V、3.3V、5V
- 具有 200ms 固定延时时间的 上电复位发生器
- 电源电流:9µA(典型值) 温度范围: -40°C 至 +85°C
- 3 引脚 SOT-23 封装
- 与 MAX809 引脚对引脚兼容

2 应用

- 工厂自动化
- 便携式和电池供电类设备
- 机顶盒
- 服务器
- 电器
- 电表
- 楼宇自动化

3 说明

TLV809 系列监控电路主要为数字信号处理器 (DSP) 以 及基于处理器的系统提供电路初始化和时序监控。较新 的 TLV809E 是引脚对引脚兼容的备选器件。

在启动期间,置位为 RESET ,前提是电源电压 (V_{DD}) 超过 1.1V。之后,监控电路就会监测 V_{DD},并使 RESET 保持有效状态,前提是 V_{DD} 保持在阈值电压 V_{IT} 以下。内部计时器将会延迟输出恢复至无效状态 (高电平)的时间,以确保系统正常复位。延时时间 $(t_{d(typ)} = 200ms)$ 从 V_{DD} 上升到高于阈值电压 V_{IT} 后开 始。一当电源电压降至 VIT 阈值电压以下时,输出再次变 为有效状态(低电平)。无需外部组件。该系列中的所 有器件均具有一个通过内部分压器设定的固定感应阈值 电压 (V_{IT})。

该产品系列专为 2.5V、3V、3.3V 以及 5V 电源电压而 设计。电路采用 3 引脚 SOT-23 封装。TLV809 器件的 额定工作温度范围为 -40°C 至 +85°C。

器件信息

器件型号	封装 ⁽¹⁾	封装尺寸(标称值)
TLV809	SOT-23 (3)、DBV	2.90mm × 1.60mm
	SOT-23 (3)、DBZ	2.92mm × 1.30mm

如需了解所有可用封装,请参阅数据表末尾的可订购产品附 (1)

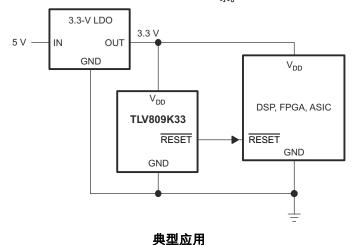




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Product Folder Links: TLV809







5 Device Comparison

表 5-1. Device Threshold Options

PRODUCT	THRESHOLD VOLTAGE
TLV809J25	2.25 V
TLV809L30	2.64 V
TLV809K33	2.93 V
TLV809I50	4.55 V

表 5-2. Device Family Comparison

DEVICE	FUNCTION
TLV803	Open-Drain, RESET Output
TLV809	Push-Pull, RESET Output
TLV810	Push-Pull, RESET Output

6 Pin Configuration and Functions

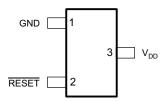


图 6-1. DBV, DBZ Packages 3-Pin SOT-23 **Top View**

Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME	1/0	DESCRIPTION
1	GND	_	Ground pin. This pin must be connected to ground with a low-impedance connection.
2	RESET	0	$\overline{RESET} \ pin. \ \overline{RESET} \ is \ an \ active \ low \ signal, \ asserting \ when \ V_{DD} \ is \ below \ the \ threshold \ voltage. When \ V_{DD} \ rises \ above \ V_{IT}, \ there \ is \ a \ delay \ time \ (t_d) \ until \ \overline{RESET} \ deasserts.$ $\overline{RESET} \ is \ a \ push-pull \ output \ stage.$
3	V _{DD}	I	Supply voltage pin. A 0.1-µF ceramic capacitor from this pin to ground is recommended to improve stability of the threshold voltage.

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7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

	3 1 3 (MIN	MAX	UNIT
V	Supply voltage ⁽²⁾		6.5	V
V_{DD}	All other pins ⁽²⁾	-0.3	6.5	
I _{OL}	Maximum low output current		5	mA
I _{OH}	Maximum high output current		– 5	mA
I _{IK}	Input clamp current ($V_I < 0$ or $V_I > V_{DD}$)		±20	mA
I _{OK}	Output clamp current (V _O < 0 or V _O > V _{DD})		±20	mA
T _A	Operating free-air temperature	-40	85	°C
T _{stg}	Storage temperature	-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

			VALUE	UNIT
V	Floatroatatio discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾		\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

at specified temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{DD}	Supply voltage	2		6	V
C _{IN}	V _{DD} bypass capacitor		0.1		μF
T _A	Operating free-air temperature range	-40		85	°C

7.4 Thermal Information

		TLV		
	THERMAL METRIC ⁽¹⁾	DBV (SOT-23)	DBZ (SOT-23)	UNIT
		3 PINS	3 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	242.1	286.9	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	213.0	105.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	123.4	124.4	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	45.7	25.8	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	130.9	107.9	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	_	_	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

⁽²⁾ All voltage values are with respect to GND. For reliable operation, do not operate the device at 6.5 V for more than t = 1000h continuously.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



7.5 Electrical Characteristics

at $T_A = -40$ °C to +85°C (unless otherwise noted); typical values are at $T_A = 25$ °C

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
			V_{DD} = 2.5 V to 6 V, I_{OH} = -500 μ A	V _{DD} - 0.2			
V _{OH}	High-level output voltage		V _{DD} = 3.3 V, I _{OH} = -2 mA	V _{DD} – 0.4			V
			V _{DD} = 6 V, I _{OH} = –4 mA	V _{DD} – 0.4			
			V _{DD} = 2 V to 6 V, I _{OH} = 500 μA			0.3	
V _{OL}	/ _{OL} Low-level output voltage		V _{DD} = 3.3 V, I _{OH} = 2 mA			0.4	V
			V _{DD} = 6 V, I _{OH} = 4 mA			0.4	
	Power-up reset voltage ⁽¹⁾		$V_{DD} \ge 1.1 \text{ V}, I_{OL} = 50 \mu\text{A}$			0.2	V
		TLV809J25		2.20	2.25	2.30	V
.,	Negative-going input	TLV809L30	$ T_{\Delta}$ = -40° C to +85°C	2.58	2.64	2.70	
V _{IT} _	threshold voltage ⁽²⁾	TLV809K33		2.93	2.99	v	
		TLV809I50		4.45	4.55	4.65	
		TLV809J25			30		
.,	Lhustanasia	TLV809L30			35		\/
V _{hys}	Hysteresis	TLV809K33			40		mV
		TLV809I50			60		
			V _{DD} = 2 V, RESET is unconnected		9	12	
I _{DD}	Supply current		V _{DD} = 6 V, RESET is unconnected		20	25	μA
Cı	Input capacitance		V _I = 0 V to V _{DD}		5		pF

7.6 Timing Requirements

at T_A = 25°C, R_L = 1 M Ω , and C_L = 50 pF

			MIN	NOM	MAX	UNIT
t _w	Pulse duration at V _{DD}	$V_{DD} = V_{IT-} + 0.2 \text{ V}, V_{DD} = V_{IT-} - 0.2 \text{ V}$	10			μs

7.7 Switching Characteristics

at $T_A = 25$ °C, $R_L = 1 M\Omega$, and $C_L = 50 pF$

	PARAMETE	R	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _d	Delay time		V _{DD} ≥ V _{IT} + 0.2 V; see 图 7-1	120	200	280	ms
t _{PHL}	Propagation (delay) time, high-to-low-level output	V _{DD} to RESET delay	V _{IL} = V _{IT} - 0.2 V, V _{IH} = V _{IT} + 0.2 V		10		μs

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 ⁽¹⁾ The lowest supply voltage at which RESET becomes active. t_{r, VDD} ≥ 15 ms/V.
 (2) To ensure best stability of the threshold voltage, place a bypass capacitor (0.1-µF ceramic) near the supply pins.



7.8 Timing Diagrams

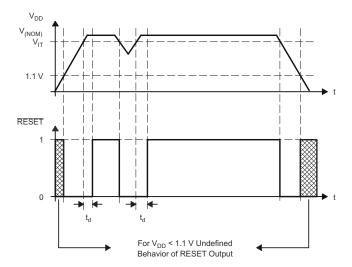


图 7-1. Timing Diagram



7.9 Typical Characteristics

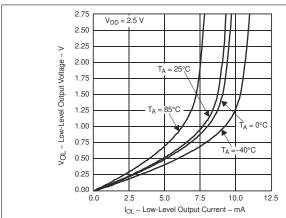


图 7-2. Low-Level Output Voltage vs Low-Level
Output Current

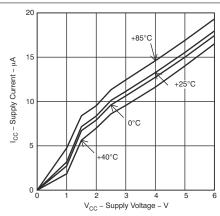


图 7-3. Supply Current vs Supply Voltage

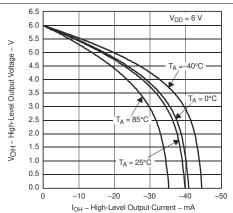


图 7-4. High-Level Output Voltage vs High-Level Output Current

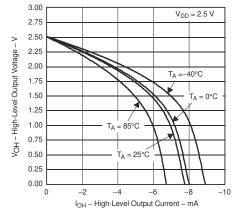


图 7-5. High-Level Output Voltage vs High-Level Output Current

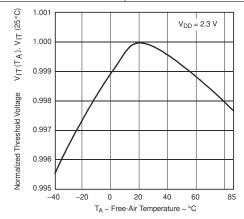


图 7-6. Normalized Input Threshold Voltage vs Free-Air Temperature at V_{DD}

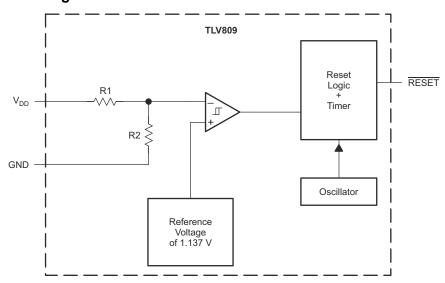


8 Detailed Description

8.1 Overview

The TLV809 is a 3-pin voltage detector with fixed detection thresholds, an active-low push-pull $\overline{\text{RESET}}$ output, and an internal timer to delay the $\overline{\text{RESET}}$ signal when V_{DD} rises above the threshold voltage.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Supply Voltage Monitoring

The device actively monitors its supply voltage to ensure that the power supply is above a certain voltage threshold.

The device offers various fixed threshold options that are approximately 10% below several standard supply voltages (2.5 V, 3.0 V, 3.3 V, 5.0 V).

8.3.2 RESET Output

The device has a RESET output to indicate the status of the input power supply.

RESET is an active low signal, asserting when V_{DD} is below the threshold voltage. When V_{DD} rises above V_{IT} , there is a delay time (t_d) until RESET deasserts.

RESET is a push-pull output stage.

8.4 Device Functional Modes

When the input supply voltage is in its recommended operating range (2 V to 6 V), the device is in a normal operational mode. In normal operational mode the device monitors V_{DD} for undervoltage detection.

When the input supply is below its recommended operating range, the device is in shutdown mode and therefore tries to assert RESET.

9 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围,TI 不担保其准确性和完整性。TI 的客 户应负责确定器件是否适用于其应用。客户应验证并测试其设计,以确保系统功能。

9.1 Application Information

9.1.1 V_{DD} Transient Rejection

The device has built-in rejection of fast transients on the V_{DD} pin. The rejection of transients depends on both the duration and the amplitude of the transient. The amplitude of the transient is measured from the bottom of the transient to the negative threshold voltage of the device, as shown in $\ensuremath{\mathbb{Z}}$ 9-1.

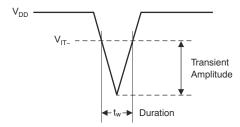


图 9-1. Voltage Transient Measurement

The device does not respond to transients that are fast duration and low amplitude or long duration and small amplitude. Transients meeting or longer than the t_w specified in the \dagger 7.6 section triggers a reset.

9.1.2 Reset During Power-Up and Power-Down

The device output is valid when V_{DD} is greater than 1.1 V. When V_{DD} is less than 1.1 V, the output transistor turns off and becomes high impedance. The voltage on the \overline{RESET} pin rises to the voltage level connected to the pullup resistor. $\boxed{8}$ 9-2 shows a typical waveform for power-up.

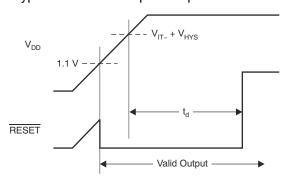


图 9-2. Power-Up Response

Product Folder Links: TLV809

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9.2 Typical Application

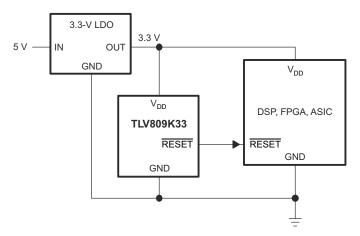


图 9-3. Monitoring a 3.3-V Supply

9.2.1 Design Requirements

The device must ensure that the supply voltage does not drop more than 15% below 3.3 V. If the supply voltage falls below 3.3 V - 15%, then the load must be disabled.

9.2.2 Detailed Design Procedure

The TLV809K33 is selected to ensure that V_{DD} is greater than 2.87 V when the load is enabled.

9.2.3 Application Curve

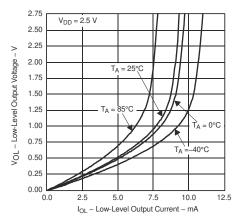


图 9-4. Low-Level Output Voltage vs Low-Level Output Current



10 Power Supply Recommendations

Power the device with a low-impedance supply. A $0.1-\mu F$ bypass capacitor from V_{DD} to ground is recommended.

11 Layout

11.1 Layout Guidelines

Place the device near the load for the input power supply, with a low-impedance connection to the power supply pins of the load to sense the supply voltage.

11.2 Layout Example

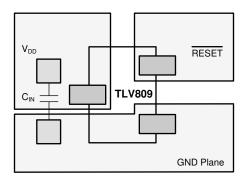


图 11-1. Example Layout



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

TLV803 Data Sheet, SBVS157

TLV810 Data Sheet, SBVS158

12.2 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料,可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者"按原样"提供。这些内容并不构成 TI 技术规范,并且不一定反映 TI 的观点;请参阅 TI 的《使用条款》。

12.3 Trademarks

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12.4 静电放电警告



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ESD 的损坏小至导致微小的性能降级,大至整个器件故障。精密的集成电路可能更容易受到损坏,这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

12.5 术语表

TI 术语表

本术语表列出并解释了术语、首字母缩略词和定义。

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
TLV809I50DBVR	Active	Production	SOT-23 (DBV) 3	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTBI
TLV809I50DBVR.A	Active	Production	SOT-23 (DBV) 3	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTBI
TLV809I50DBVT	Active	Production	SOT-23 (DBV) 3	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTBI
TLV809I50DBVT.A	Active	Production	SOT-23 (DBV) 3	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTBI
TLV809I50DBZR	Active	Production	SOT-23 (DBZ) 3	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	BCMV
TLV809I50DBZR.A	Active	Production	SOT-23 (DBZ) 3	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BCMV
TLV809I50DBZT	Active	Production	SOT-23 (DBZ) 3	250 SMALL T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	BCMV
TLV809I50DBZT.A	Active	Production	SOT-23 (DBZ) 3	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BCMV
TLV809J25DBVR	Active	Production	SOT-23 (DBV) 3	3000 LARGE T&R	Yes	NIPDAU NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTCI
TLV809J25DBVR.A	Active	Production	SOT-23 (DBV) 3	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTCI
TLV809J25DBVT	Active	Production	SOT-23 (DBV) 3	250 SMALL T&R	Yes	NIPDAU NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTCI
TLV809J25DBVT.A	Active	Production	SOT-23 (DBV) 3	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTCI
TLV809J25DBZR	Active	Production	SOT-23 (DBZ) 3	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	BCMT
TLV809J25DBZR.A	Active	Production	SOT-23 (DBZ) 3	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BCMT
TLV809J25DBZT	Active	Production	SOT-23 (DBZ) 3	250 SMALL T&R	Yes	NIPDAU SN NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	BCMT
TLV809J25DBZT.A	Active	Production	SOT-23 (DBZ) 3	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BCMT
TLV809K33DBVR	Active	Production	SOT-23 (DBV) 3	3000 LARGE T&R	Yes	NIPDAU NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTRI
TLV809K33DBVR.A	Active	Production	SOT-23 (DBV) 3	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTRI
TLV809K33DBVT	Active	Production	SOT-23 (DBV) 3	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTRI
TLV809K33DBVT.A	Active	Production	SOT-23 (DBV) 3	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTRI
TLV809K33DBZR	Active	Production	SOT-23 (DBZ) 3	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	BCMX
TLV809K33DBZR.A	Active	Production	SOT-23 (DBZ) 3	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BCMX
TLV809K33DBZT	Active	Production	SOT-23 (DBZ) 3	250 SMALL T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	BCMX
TLV809K33DBZT.A	Active	Production	SOT-23 (DBZ) 3	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BCMX
TLV809L30DBVR	Active	Production	SOT-23 (DBV) 3	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTXI
TLV809L30DBVR.A	Active	Production	SOT-23 (DBV) 3	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTXI
TLV809L30DBVT	Active	Production	SOT-23 (DBV) 3	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTXI
TLV809L30DBVT.A	Active	Production	SOT-23 (DBV) 3	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTXI



-40 to 85

-40 to 85

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BCMZ

BCMZ



TLV809L30DBZT

TLV809L30DBZT.A

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Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
TLV809L30DBZR	Active	Production	SOT-23 (DBZ) 3	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	BCMZ
TLV809L30DBZR.A	Active	Production	SOT-23 (DBZ) 3	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BCMZ

Yes

Yes

SN

SN

Level-1-260C-UNLIM

Level-1-260C-UNLIM

250 | SMALL T&R

250 | SMALL T&R

Active

Active

Production

Production

SOT-23 (DBZ) | 3

SOT-23 (DBZ) | 3

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽¹⁾ Status: For more details on status, see our product life cycle.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



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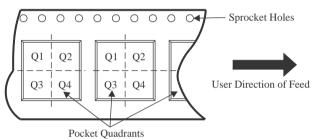
TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV809I50DBVR	SOT-23	DBV	3	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV809I50DBVT	SOT-23	DBV	3	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV809I50DBZR	SOT-23	DBZ	3	3000	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV809I50DBZR	SOT-23	DBZ	3	3000	180.0	8.4	2.9	3.35	1.35	4.0	8.0	Q3
TLV809I50DBZT	SOT-23	DBZ	3	250	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV809J25DBVR	SOT-23	DBV	3	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV809J25DBVT	SOT-23	DBV	3	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV809J25DBZR	SOT-23	DBZ	3	3000	180.0	8.4	2.9	3.35	1.35	4.0	8.0	Q3
TLV809J25DBZT	SOT-23	DBZ	3	250	180.0	8.4	2.9	3.35	1.35	4.0	8.0	Q3
TLV809J25DBZT	SOT-23	DBZ	3	250	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV809K33DBVR	SOT-23	DBV	3	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV809K33DBVT	SOT-23	DBV	3	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV809K33DBZR	SOT-23	DBZ	3	3000	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV809K33DBZR	SOT-23	DBZ	3	3000	180.0	8.4	2.9	3.35	1.35	4.0	8.0	Q3
TLV809K33DBZT	SOT-23	DBZ	3	250	180.0	8.4	2.9	3.35	1.35	4.0	8.0	Q3
TLV809K33DBZT	SOT-23	DBZ	3	250	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3



PACKAGE MATERIALS INFORMATION

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Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV809L30DBVR	SOT-23	DBV	3	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV809L30DBVT	SOT-23	DBV	3	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV809L30DBZR	SOT-23	DBZ	3	3000	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV809L30DBZT	SOT-23	DBZ	3	250	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3



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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV809I50DBVR	SOT-23	DBV	3	3000	180.0	180.0	18.0
TLV809I50DBVT	SOT-23	DBV	3	250	180.0	180.0	18.0
TLV809I50DBZR	SOT-23	DBZ	3	3000	180.0	180.0	18.0
TLV809I50DBZR	SOT-23	DBZ	3	3000	210.0	185.0	35.0
TLV809I50DBZT	SOT-23	DBZ	3	250	180.0	180.0	18.0
TLV809J25DBVR	SOT-23	DBV	3	3000	180.0	180.0	18.0
TLV809J25DBVT	SOT-23	DBV	3	250	180.0	180.0	18.0
TLV809J25DBZR	SOT-23	DBZ	3	3000	210.0	185.0	35.0
TLV809J25DBZT	SOT-23	DBZ	3	250	210.0	185.0	35.0
TLV809J25DBZT	SOT-23	DBZ	3	250	180.0	180.0	18.0
TLV809K33DBVR	SOT-23	DBV	3	3000	180.0	180.0	18.0
TLV809K33DBVT	SOT-23	DBV	3	250	180.0	180.0	18.0
TLV809K33DBZR	SOT-23	DBZ	3	3000	180.0	180.0	18.0
TLV809K33DBZR	SOT-23	DBZ	3	3000	210.0	185.0	35.0
TLV809K33DBZT	SOT-23	DBZ	3	250	210.0	185.0	35.0
TLV809K33DBZT	SOT-23	DBZ	3	250	180.0	180.0	18.0
TLV809L30DBVR	SOT-23	DBV	3	3000	180.0	180.0	18.0
TLV809L30DBVT	SOT-23	DBV	3	250	180.0	180.0	18.0

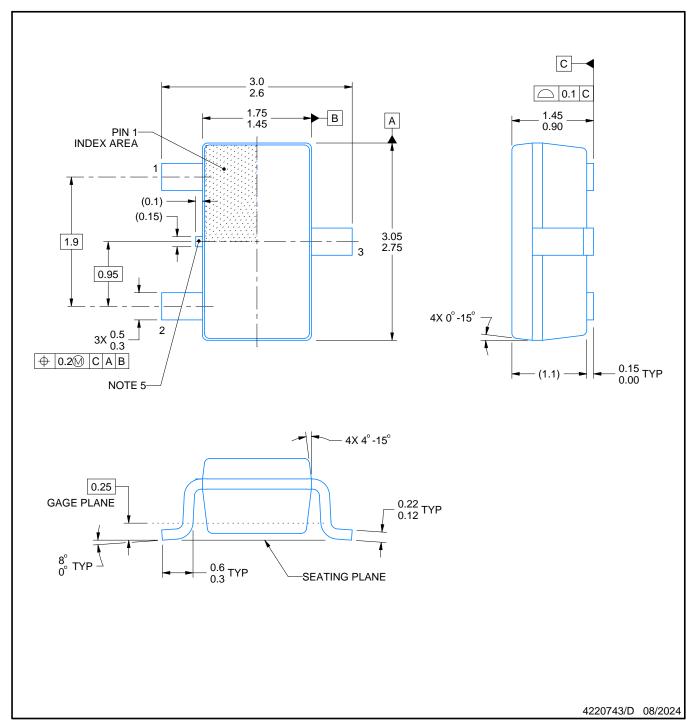


PACKAGE MATERIALS INFORMATION

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV809L30DBZR	SOT-23	DBZ	3	3000	180.0	180.0	18.0
TLV809L30DBZT	SOT-23	DBZ	3	250	180.0	180.0	18.0



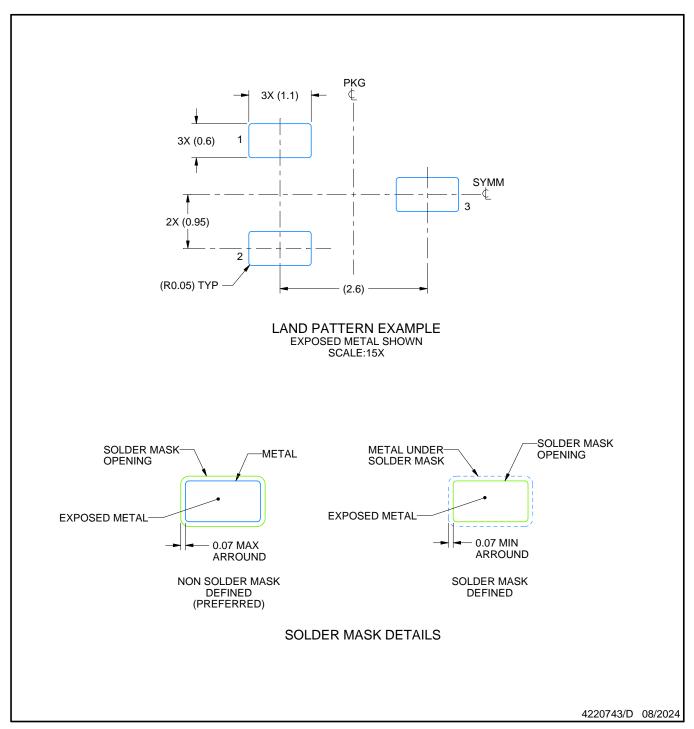


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Refernce JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



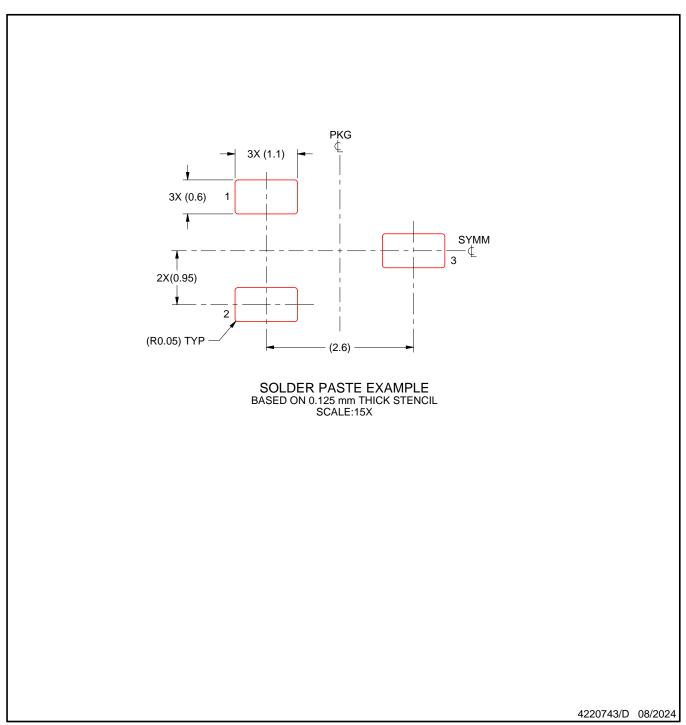


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 Reference JEDEC registration TO-236, except minimum foot length.

- 4. Support pin may differ or may not be present.
- 5. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side





NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



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